SHIPLEY 1813 POSITIVE TONE PHOTORESIST PROCESS

1. Substrate Dehydration: 10-minutes @ 110°C.
2. Adhesion Promoter Coating:
   Apply puddle HMDS on entire wafer and wait 5-10 seconds
   Spinning for 45 seconds @ 3500 RPM.
2. Photoresist coating.
   Cover about 50% of the substrate starting at the center
   Spread: 450 rpm 3 Second
   Spin: 45-sec @ 4000RPM for a resist for thickness of 1.3um
   Soft bake: vacuum hot plate at a temperature between at 1150°C for 60 seconds
   Exposure: 150 mJ (changes with transparent field of the mask)
   Develop: MF 319 for 45 second with agitation
   Rinse and Dry: Rinse with DI water for 30-60 seconds and dry with blowing nitrogen.

For More information: talk to NCNC staff or refer to data sheet